



Handwritten initials "DW" and a dollar sign "\$".

TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	10/642,305	
	Filing Date	August 18, 2003	
	First Named Inventor	Hongyong ZHANG et al.	
	Group Art Unit	2811	
	Examiner Name	Douglas W. Owens	
Total Number of Pages in This Submission		Attorney Docket Number	740756-2646

ENCLOSURES (check all that apply)		
<input checked="" type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input type="checkbox"/> Application Data Sheet <input type="checkbox"/> Request for Corrected Filing Receipt with Enclosures <input type="checkbox"/> A self-addressed prepaid postcard for acknowledging receipt <input type="checkbox"/> Other Enclosure(s) (please identify below):
Remarks		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 19-2380 for the above identified docket number.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT	
Firm or Individual name	Jeffrey L. Costellia – Reg. No. 35,483 Nixon Peabody LLP 401 9 th Street, N.W. Suite 900 Washington, D.C. 20004-2128
Signature	
Date	March 2, 2007

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March 2, 2007 Date	_____ Signature Pamela Patrick Typed or printed name



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hongyong ZHANG et al.
Serial No. 10/642,305
Filed: August 18, 2003
For: THIN-FILM TRANSISTOR

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Examiner: Douglas W. Owens
Group Art Unit: 2811

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initial a copy of this form be returned to the undersigned.

Applicants have filed Information Disclosure Statements on March 30, 2005; August 12, 2005; September 16, 2005; February 3, 2006; and June 1, 2006 to submit information from a pending litigation, namely, Case No. CV 04-4783 TJX (AJW). The litigation involves U.S. Patent No. 6,177,302 and U.S. Patent No. 6,566,175 which are in the same family as co-pending application Serial No. 10/408,891. The '891 application is not in the same family as the instant application. Further, the litigation involves U.S. Patent No. 5,532,291 which is not in the same family as the instant application. Moreover, the litigation involves U.S. Patent Nos. 5,313,075 and 6,607,947 which are in the same family as the instant application, as previously noted, and pending U.S. Application No. 10/401,891. The documents cited herein relate to this litigation.

03/05/2007 MAHME1 00000099 192380 10642385
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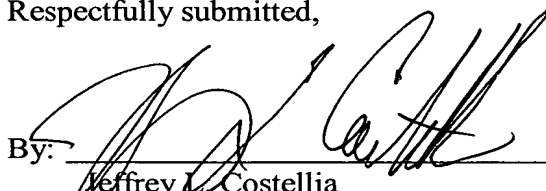
Sheet 1-1 (List 1) relates to documents from the above noted litigation. Sheets 1-5 (List 2-3) relates to document which were attached to Document Nos. 7 and 8 from Sheet 1-1.

Except for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§ 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account No. 19-2380.

The Commissioner is hereby authorized to charge the Deposit Account No. 19-2380 in the amount of \$180 to comply with the provisions of 37 C.F.R. § 1.97(c).

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

By: 
Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
Suite 900
401 9th Street, N.W.
Washington, DC 20004-2128
Telephone: (202) 585-8000

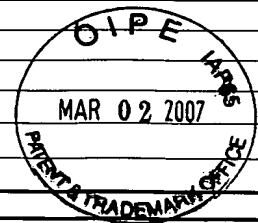
FEE TRANSMITTAL FOR FY 2005

Patent fees are subject to annual revision.

☐ Applicant claims small entity status. See 37 CFR 1.27

Complete if Known

Application Number 10/642,305
Filing Date August 18, 2003
First Named Inventor Hongyong ZHANG et al.
Examiner Name Douglas W. Owens
Art Unit 2811
Attorney Docket No. 740756-2646



TOTAL AMOUNT OF PAYMENT (\$180.00)

METHOD OF PAYMENT (check all that apply)

☐ Check ☐ Credit Card ☐ Money Order ☐ Other ☐ None

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FEE CALCULATION

1. BASIC FILING FEE

Large Entity Fee Code	Large Entity Fee (\$)	Small Entity Fee Code	Small Entity Fee (\$)	Fee Description	Fee Paid
1001	300	2001	150	Utility filing fee	
1002	200	2002	100	Design filing fee	
1003	200	2003	100	Plant filing fee	
1004	300	2004	150	Reissue filing fee	
1005	200	2005	100	Provisional filing fee	

SUBTOTAL (1) (\$ 0)

2. EXTRA CLAIM FEES FOR UTILITY AND REISSUE

Total Claims	Extra Claims	Fee from below	Fee Paid
20**	X		0
Independent Claims	-3**	X	0
Multiple Dependent	X		0

Large Entity Fee Code	Large Entity Fee (\$)	Small Entity Fee Code	Small Entity Fee (\$)	Fee Description
1202	50	2202	25	Claims in excess of 20
1201	200	2201	100	Independent claims in excess of 3
1203	360	2203	180	Multiple dependent claim, if not paid
1204	200	2204	100	** Reissue independent claims over original patent
1205	50	2205	25	** Reissue claims in excess of 20 and over original patent

SUBTOTAL (2) (\$ 0)

**or number previously paid, if greater; For Reissues, see above

FEE CALCULATION (continued)

3. ADDITIONAL FEES

Large Entity Fee Code	Large Entity Fee (\$)	Small Entity Fee Code	Small Entity Fee (\$)	Fee Description
1051	130	2051	65	Surcharge - late filing fee or oath
1052	50	2052	25	Surcharge - late provisional filing fee or cover sheet
1053	130	1053	130	Non-English specification
1812	2,520	1812	2,520	For filing a request for <i>ex parte</i> reexamination
1804	920*	1804	920*	Requesting publication of SIR prior to Examiner action
1805	1,840*	1805	1,840*	Requesting publication of SIR after Examiner action
1251	120	2251	60	Extension for reply within first month
1252	450	2252	225	Extension for reply within second month
1253	1,020	2253	510	Extension for reply within third month
1254	1,590	2254	795	Extension for reply within fourth month
1255	2,160	2255	1,080	Extension for reply within fifth month
1401	500	2401	250	Notice of Appeal
1402	500	2402	250	Filing a brief in support of an appeal
1403	1,000	2403	500	Request for oral hearing
1451	1,510	1451	1,510	Petition to institute a public use proceeding
1452	500	2452	250	Petition to revive - unavoidable
1453	1,500	2453	750	Petition to revive - unintentional
1501	1,400	2501	700	Utility issue fee (or reissue)
1502	800	2502	400	Design issue fee
1503	1,100	2503	550	Plant issue fee
1460	130	1460	130	Petitions to the Commissioner
1807	50	1807	50	Processing fee under 37 CFR 1.17(q)
1806	180	1806	180	Submission of Information Disclosure Stmt
8021	40	8021	40	Recording each patent assignment per property (times number of properties)
1809	790	2809	395	Filing a submission after final rejection (37 CFR 1.129(a))
1810	790	2810	395	For each additional invention to be examined (37 CFR 1.129(b))
1801	790	2801	395	Request for Continued Examination (RCE)
1802	900	1802	900	Request for expedited examination of a design application

Other fee (specify) _____

*Reduced by Basic Filing Fee Paid

SUBTOTAL (3) (\$180.00)

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Name (Print/Type) Jeffrey J. Costellia

Signature

Registration No. (Attorney/Agent)

35,483

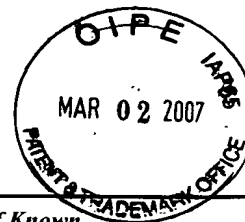
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(List 2-3)

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/642,305		
		Filing Date	August 18, 2003		
		First Named Inventor	Hongyong ZHANG et al.		
		Art Unit	2811		
		Examiner Name	Douglas W. Owens		
Sheet	1	of	5	Attorney Docket Number	740756-2646

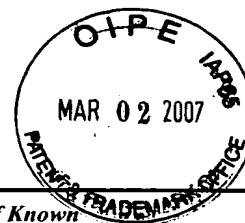
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1	PERRIN, J. et al., "Mass-Spectrometric Study of NF ₃ Plasma-Etching of Silicon", <u>Plasma Chemistry and Plasma Processing</u> , Vol. 10, No. 4, (1990) pp. 571-587	
	2	GROVE, A.S., "Physics and Technology of Semiconductor Devices", Wiley (New York), (1967), p. 334.	
	3	GORDON, R. "Chemical Vapor Deposition of Coatings on Glass", <u>Journal of Non-Crystalline Solids</u> , Vol. 218, (1997), pp. 81-91.	
	4	BALK, P. et al. "Phosphosilicate Glass Stabilization of FET Devices", <u>Proceedings of the IEEE</u> , Vol. 57, No. 9, (September 1969), pp.1558-1563.	
	5	PLUMMER et al.; "Silicon VLSI Technology: Fundamentals, Practice and Modeling"	
	6	NICOLLIAN, E.H. et al.; "MOS (Metal Oxide Semiconductor Physics and Technology)", Wiley (New York) p. 774.	
	7	Sze S.M. (Author ADAMS, A.C.), "VLSI Technology" Wiley, (New York) (1983) pp. 93-129.	
	8	KRIEGLER, R.J., "Neutralization of Na ⁺ Ions in HCl-Grown SiO ₂ ", <u>Applied Physics Letters</u> , Vol. 20, No. 11, (June 1, 1972), pp. 449-541.	
	9	DEAL, B.E. et al. "Chlorine Concentration Profiles in 0.2 -HCl and H ₂ O- HCl Thermal Silicon-Oxides Using Sims Measurements", <u>Journal of the Electrochemical Society</u> , Vol. 125, No. 12, (December 1978), pp. 2024-2027.	
	10	ROHATGI, A. et al. "Sodium Passivation in HCl Oxide-Films on Si", <u>Applied Physics Letters</u> , Vol. 30, No. 2, (January 15, 1977) pp. 104-106.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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(List 2-3)

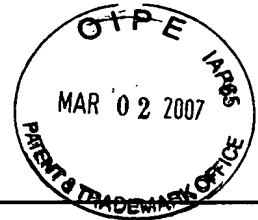
Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	10/642,305
		Filing Date	August 18, 2003
		First Named Inventor	Hongyong ZHANG et al.
		Art Unit	2811
		Examiner Name	Douglas W. Owens
		Attorney Docket Number	740756-2646
Sheet	2	of	5

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ⁶	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ROHATGI A., et al. " <u>Chlorine Incorporation in HCl Oxides</u> ", <u>Journal of The Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 143-148.	
		ROHATGI A., et al. " <u>Mobile Sodium Ion Passivation in HCl Oxides</u> ," <u>Journal of the Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 149-154.	
		WILLIAMS, R. et al. " <u>Mobile Fluoride Ions in SiO₂</u> ", <u>Journal of Applied Physics</u> , Vol. 46, No. 2 (February 1975) pp. 695-698	
		LEE, M.K. et al. " <u>Control of Silicon Dioxide Properties by RF Sputtering</u> ", <u>Journal of the Electrochemical Society</u> , Vol. 130, No. 3, (March 1983) pp. 685-859	
		DASILVA, E.F. et al. " <u>Radiation Response of MOS Capacitors Containing Fluorinated Oxides</u> , <u>IEEE Transaction on Nuclear Science</u> , Vol. 34, No. 6, (December 1987) pp. 1190-1195.	
		NISHIOKA, Y. et al. " <u>Dramatic Improvement of Hot-Electron-Induced Interface Degradation in MOS Structures Containing F or Cl in SiO₂</u> ", <u>IEEE Electron Device Letters</u> , Vol. 9, No. 1, (Jan. 1988), pp. 38-40.	
		NISHIOKA, Y. et al. " <u>Dielectric Characteristics of Fluorinated Ultradry SiO₂</u> " <u>Applied Physics Letters</u> , Vol. 54, No. 12, (March 20, 1989), pp. 1127-1129	
		NISHIOKA, Y. et al. " <u>Hot-Electron Hardened Si-Gate MOSFET Utilizing F-Implantation</u> ", <u>IEEE Electron Device Letters</u> , Vol. 10, No. 4, (April 1989), pp. 141-143.	
		BRUNO, G. et al. " <u>Study of the NF₃ Plasma Cleaning of Reactors for Amorphous-Silicon Deposition</u> ", <u>Journal of Vacuum Science & Technology A</u> , Vol. 12, No. 3, (1994), pp. 690-698	
		JANSEN, F. et al. " <u>Contamination Effects in Glow-Discharge Deposition Systems</u> ", <u>Journal of Vacuum Science & Technology A</u> , Vol. 6, No. 1, (1988), pp. 13-18	
Examiner Signature			Date Considered

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				Application Number	10/642,305
				Filing Date	August 18, 2003
				First Named Inventor	Hongyong ZHANG et al.
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				Examiner Name	Douglas W. Owens
Sheet	3	of	5	Attorney Docket Number	740756-2646

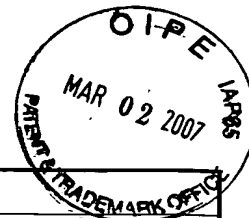
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
		KARULKAR, P.C. et al., “ <i>XPS AES Investigation of Cross Contamination in a Plasma Etcher</i> ”, <u>Journal of Vacuum Science & Technology B</u> , Vol. 3, No. 3, (1985), pp. 889-891		
		Exhibit 7, Asserted Claim Chart – Sano Reference, JP 64-35959		
		FRANCOIS-SAINT-CYR, et al. “ <i>Diffusion of 18 elements implanted into thermally grown SiO₂</i> ”, <u>Journal of Applied Physics</u> , Vol. 94, No. 12, (December 15, 2003), pp. 7433-7439		
		DATAR, S.A. et al. “ <i>AMS Studies of the Diffusion of Chlorine in Silicon-Wafers</i> ” <u>Nuclear Instruments & Methods in Physics Research- B 99</u> - Beam Interactions with Materials and Atoms, (1995), pp. 549-552		
		TSENG, H.H. et al. “ <i>Fluorine Diffusion on a Polysilicon Grain-Boundary Network in Relation to Boron Penetration from P+ Gates</i> ”, <u>IEEE Electron Device Letters</u> , Vol. 13, No. 1, (January 1992), pp. 14-16		
		TROXELL, JOHN R. et al. “ <i>Polycrystalline Silicon Thin-Film Transistors on a Novel 800°C Glass Substrate</i> ”, <u>IEEE Electron Device Letters</u> , Vol. 7, No. 11, (November 1986), pp. 597-599		
		ERMOLIEFF, A. et al. “ <i>XPS Studies of Contamination of Reactor and Silicon Surfaces Caused by Reactive Ion Etching</i> ”, <u>Semiconductor Science and Technology</u> , Vol. 6, (1991), pp. 290-295		
		ERMOLIEFF, A. et al. “ <i>X-Ray Photoelectron-Spectroscopy Studies of Contamination and Cleaning of Surfaces Exposed to a Fluorocarbon Plasma</i> ”, <u>Journal of Vacuum Science & Technology A</u> , Vol. 9, No. 6, (November/December 1991), pp. 2900-2906		

Examiner Signature		Date Considered	
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Sheet	4	of	5	Attorney Docket Number	740756-2646

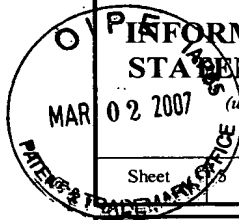
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
		HUGHES, C. et al. <i>"In-situ HDP-CVD Process Diagnostics Based on Quadrupole Mass Spectrometry"</i> , (IMEC Leuven, Belgium)		
		IQBAL, Z. et al. <i>"Raman scattering from hydrogenated microcrystalline and amorphous silicon"</i> , <u>J. Phys. C. Solid State Phys.</u> , Vol. 15 (1982) pp. 377-392		
		JENG, S.P. et al. <i>"Anomalous Diffusion of Fluorine in Silicon"</i> , <u>Applied Physics Letters</u> , Vol. 61, No. 11, (September 14, 1992), pp. 1310-1312		
		YOUNG, N.D. et al. <i>"Mobile ion instabilities in polycrystalline silicon thin film transistors"</i> <u>Applied Surface Science</u> , Vol. 39, (1989), pp. 364-367		
		SAMESHIMA et al. <i>"XeCl Excimer Annealing Used to Fabricate Poly-Si TFT's"</i> , <u>IEEE Electronic Device Letters</u> , Vol. 7, No. 5, (May 1986), pp. 276-278		
		KAKKAD et al. <i>"Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon"</i> , <u>J. Applied Physics</u> , Vol. 65, No. 5, (March 1, 1989), pp. 2069-2072		
		PINARBASI, M. et al., <i>"Hydrogenated Amorphous Silicon Films Deposited by DC Planar Magnetron Reactive Sputtering"</i> , <u>Superlattices and Microstructure</u> , Vol. 3, No. 4, (1987) pp. 331-340		
		MADAN, A. et al. <i>"Characterization of Schottky Barriers"</i> , <u>The Physics and Applications of Amorphous Semiconductors</u> , Academic Press, pp. 193-197		
		MADAN et al. <i>"Use of PECVD System in Thin Film Technology"</i> , Workshop on Industrial Plasma Applications, pp. 1-10		
		MALEY, N. et al. <i>"Infrared absorption and thermal evolution study and hydrogen bonding in a-SiH"</i> , <u>Journal of Vacuum Science & Technology</u> , Vol. 7, No. 3, (May/June 1989), pp. 1267-1270		

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		Art Unit	2811
		Examiner Name	Douglas W. Owens
Sheet 1 of 5	Attorney Docket Number	740756-2646	

U.S. PATENT DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-4,007,294	02/08/1977	Woods et al.	
		US-4,485,146	11/27/1984	Mizuhashi et al.	
		US-4,657,616	04/14/1987	Benzing et al.	
		US-4,786,352	11/22/1988	Benzing	
		US-4,851,363	07/25/1989	Troxell et al.	
		US-7,097,716 B2	08/29/2006	Barnes et al.	
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 64-35959	02/07/1989			
		JP 01-268064	10/25/1989			FULL

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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(List 1)

Substitute for form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/642,305		
		Filing Date	August 18, 2003		
		First Named Inventor	Hongyong ZHANG et al.		
		Art Unit	2811		
		Examiner Name	Douglas W. Owens		
Sheet	1	of	1	Attorney Docket Number	740756-2646

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1	Toppoly's Opposition Claim Construction Brief, May 30, 2006	
	2	Declaration of Hector G. Gallegos in Support of Toppoly Optoelectronics Corp's. Opposition Claim Construction Brief, May 30, 2006	
	3	Plaintiff and Counterclaim Defendant Semiconductor Energy Laboratory Co., Ltd.'s Memorandum of Points and Authorities in Opposition to Defendants' and Counterclaim Plaintiffs' Claim Construction Brief (signed on 05/26/2006), May 30, 2006	
	4	Supplemental Declaration of Reginald J. Hill in Support of Semiconductor Energy Laboratory Co., Ltd.'s Claim Constructions (signed on 05/26/2006), May 30, 2006	
	5	Toppoly Optoelectronics Corp.'s Supplemental Response to Semiconductor Energy Laboratory Co., Ltd.'s Interrogatory No. 4, June 21, 2006	
	6	Order: Claim Construction Ruling, July 25, 2006	
	7	Invalidity Report of Professor Gottlieb S. Oehrlein, September 22, 2006	
	8	Expert on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006	

Examiner Signature		Date Considered	
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